

# CSD13385F5 12-V N-Channel FemtoFET™ MOSFET

## 1 Features

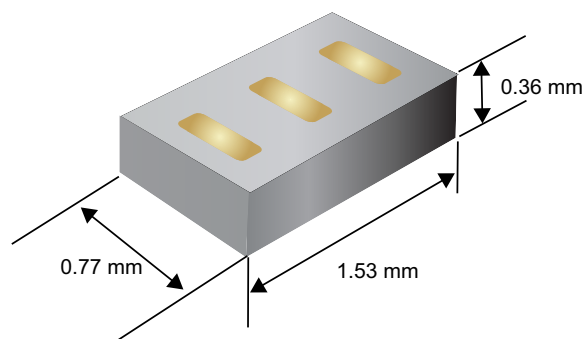
- Low on resistance
- Low  $Q_g$  and  $Q_{gd}$
- Ultra-small footprint
  - 1.53 mm × 0.77 mm
- Low profile
  - 0.36-mm height
- Integrated ESD protection diode
  - Rated > 4-kV HBM
  - Rated > 2-kV CDM
- Lead and halogen free
- RoHS compliant

## 2 Applications

- Optimized for industrial load switch applications
- Optimized for general purpose switching applications

## 3 Description

This 12-V, 15-mΩ, N-Channel FemtoFET™ MOSFET technology is designed and optimized to minimize the footprint in many handheld and mobile applications. This technology is capable of replacing standard small signal MOSFETs while providing a significant reduction in footprint size.



Typical Part Dimensions

## Product Summary

$T_A = 25^\circ\text{C}$		TYPICAL VALUE	UNIT
$V_{DS}$	Drain-to-Source Voltage	12	V
$Q_g$	Gate Charge Total (4.5 V)	3.9	nC
$Q_{gd}$	Gate Charge Gate-to-Drain	0.39	nC
$R_{DS(on)}$	Drain-to-Source On Resistance	$V_{GS} = 1.8\text{ V}$	26
		$V_{GS} = 2.5\text{ V}$	18
		$V_{GS} = 4.5\text{ V}$	15
$V_{GS(th)}$	Threshold Voltage	0.8	V

## Device Information<sup>(1)</sup>

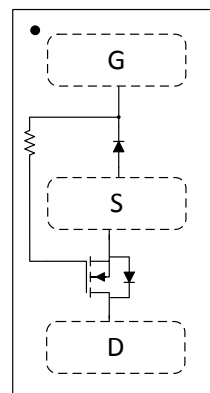
DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD13385F5	3000	7-Inch Reel	Femto	Tape
CSD13385F5T	250		1.53-mm × 0.77-mm SMD Lead Less	and Reel

- (1) For all available packages, see the orderable addendum at the end of the data sheet.

## Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$		VALUE	UNIT
$V_{DS}$	Drain-to-Source Voltage	12	V
$V_{GS}$	Gate-to-Source Voltage	8	V
$I_D$	Continuous Drain Current <sup>(1)</sup>	4.3	A
	Continuous Drain Current <sup>(2)</sup>	7.1	
$I_{DM}$	Pulsed Drain Current <sup>(1) (3)</sup>	41	A
$P_D$	Power Dissipation <sup>(1)</sup>	0.5	W
	Power Dissipation <sup>(2)</sup>	1.4	
$V_{(ESD)}$	Human-Body Model (HBM)	4	kV
	Charged-Device Model (CDM)	2	
$T_J, T_{stg}$	Operating Junction, Storage Temperature	–55 to 150	°C

- (1) Min Cu, typical  $R_{\theta JA} = 245^\circ\text{C/W}$ .  
 (2) Max Cu, typical  $R_{\theta JA} = 90^\circ\text{C/W}$ .  
 (3) Pulse duration ≤ 100 μs, duty cycle ≤ 1%.



Top View



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## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

<b>Changes from Revision A (May 2017) to Revision B (February 2022)</b>	<b>Page</b>
• Changed ultra-low profile bullet from 0.35 mm to 0.36 mm in height.....	1
• Updated ultra-low profile image height from 0.35 mm to 0.36 mm.....	1
• Changed ultra-low profile image height from 0.35 mm to 0.36 mm.....	8
• Added FemtoFET Surface Mount Guide note.....	9

<b>Changes from Revision * (October 2016) to Revision A (May 2017)</b>	<b>Page</b>
• Changed $I_{DSS}$ and $I_{GSS}$ unit value from $\mu A$ to nA in the <i>Electrical Characteristics</i> table. ....	3

## 5 Specifications

### 5.1 Electrical Characteristics

$T_A = 25^\circ\text{C}$  (unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
STATIC CHARACTERISTICS							
BV <sub>DSS</sub>	Drain-to-source voltage	V <sub>GS</sub> = 0 V, I <sub>DS</sub> = 250 μA	12			V	
I <sub>DSS</sub>	Drain-to-source leakage current	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 9.6 V	50			nA	
I <sub>GSS</sub>	Gate-to-source leakage current	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 8 V	25			nA	
V <sub>GS(th)</sub>	Gate-to-source threshold voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>DS</sub> = 250 μA	0.5	0.8	1.2	V	
R <sub>DS(on)</sub>	Drain-to-source on resistance	V <sub>GS</sub> = 1.8 V, I <sub>DS</sub> = 0.1 A	26			50	mΩ
		V <sub>GS</sub> = 2.5 V, I <sub>DS</sub> = 0.9 A	18			23	
		V <sub>GS</sub> = 4.5 V, I <sub>DS</sub> = 0.9 A	15			19	
g <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 1.2 V, I <sub>DS</sub> = 0.9 A	11.3			S	
DYNAMIC CHARACTERISTICS							
C <sub>iss</sub>	Input capacitance	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 6 V, f = 1 MHz	519			674	pF
C <sub>oss</sub>	Output capacitance		305			396	pF
C <sub>rss</sub>	Reverse transfer capacitance		29			38	pF
R <sub>G</sub>	Series gate resistance		20			Ω	
Q <sub>g</sub>	Gate charge total (4.5 V)	V <sub>DS</sub> = 6 V, I <sub>DS</sub> = 0.9 A	3.9			5.0	nC
Q <sub>gd</sub>	Gate charge gate-to-drain		0.39				nC
Q <sub>gs</sub>	Gate charge gate-to-source		0.74				nC
Q <sub>g(th)</sub>	Gate charge at V <sub>th</sub>		0.46				nC
Q <sub>oss</sub>	Output charge	V <sub>DS</sub> = 6 V, V <sub>GS</sub> = 0 V	2.5				nC
t <sub>d(on)</sub>	Turnon delay time	V <sub>DS</sub> = 6 V, V <sub>GS</sub> = 4.5 V, I <sub>DS</sub> = 0.9 A, R <sub>G</sub> = 2 Ω	7				ns
t <sub>r</sub>	Rise time		10				ns
t <sub>d(off)</sub>	Turnoff delay time		33				ns
t <sub>f</sub>	Fall time		10				ns
DIODE CHARACTERISTICS							
V <sub>SD</sub>	Diode forward voltage	I <sub>SD</sub> = 0.9 A, V <sub>GS</sub> = 0 V	0.67			1.0	V

### 5.2 Thermal Information

$T_A = 25^\circ\text{C}$  (unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance <sup>(1)</sup>		90		$^\circ\text{C/W}$
	Junction-to-ambient thermal resistance <sup>(2)</sup>		245		

- (1) Device mounted on FR4 material with 1-in<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz (0.071-mm) thick Cu.  
 (2) Device mounted on FR4 material with minimum Cu mounting area.

### 5.3 Typical MOSFET Characteristics

$T_A = 25^\circ\text{C}$  (unless otherwise stated)

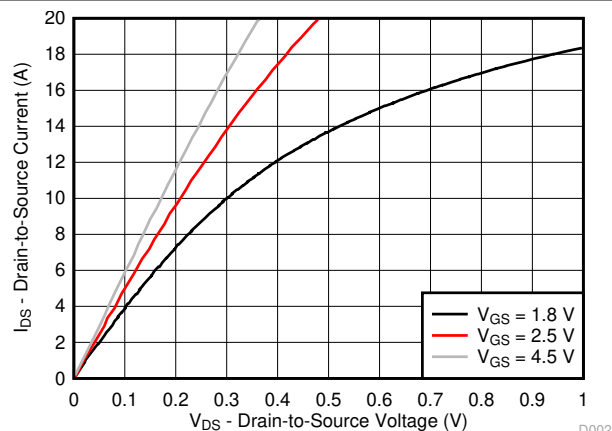


Figure 5-1. Saturation Characteristics

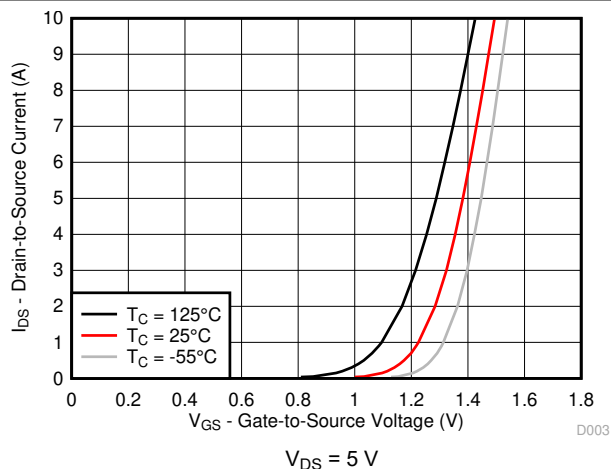


Figure 5-2. Transfer Characteristics

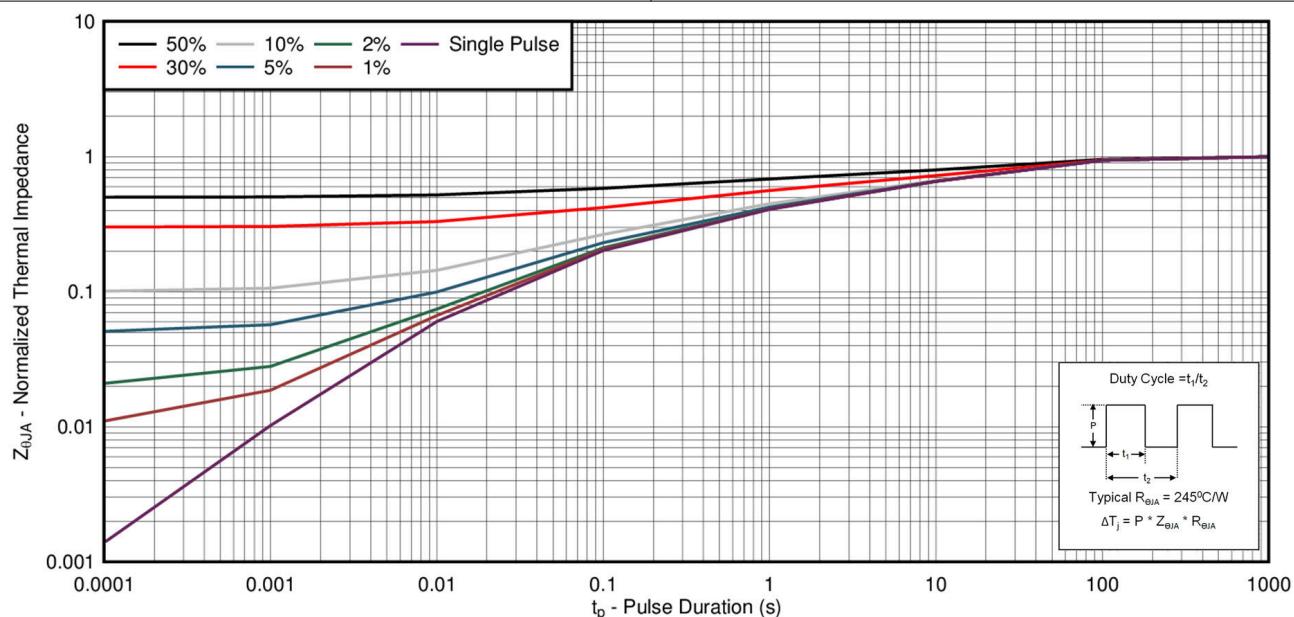


Figure 5-3. Transient Thermal Impedance

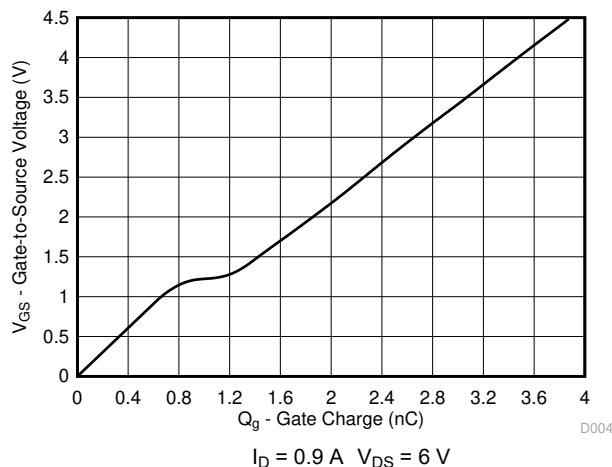


Figure 5-4. Gate Charge

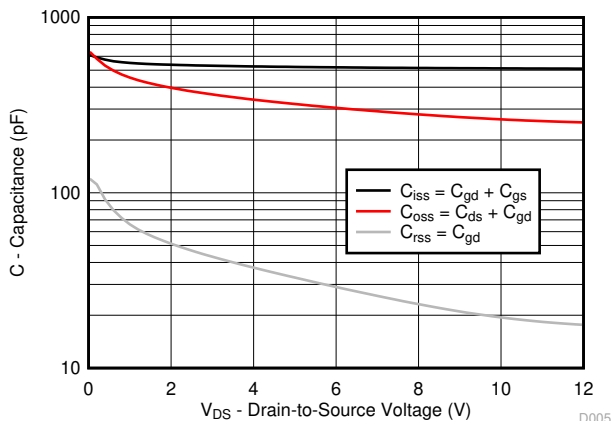
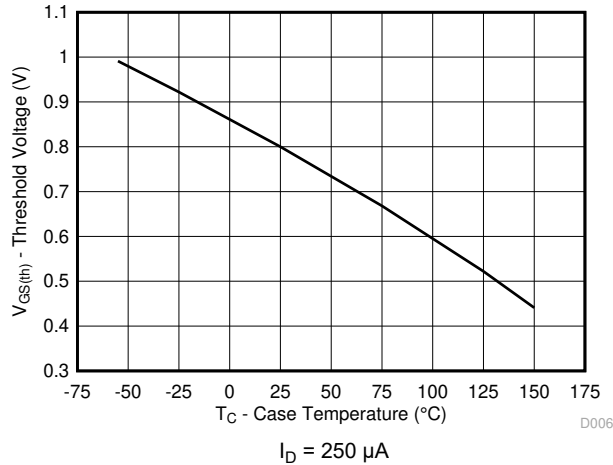
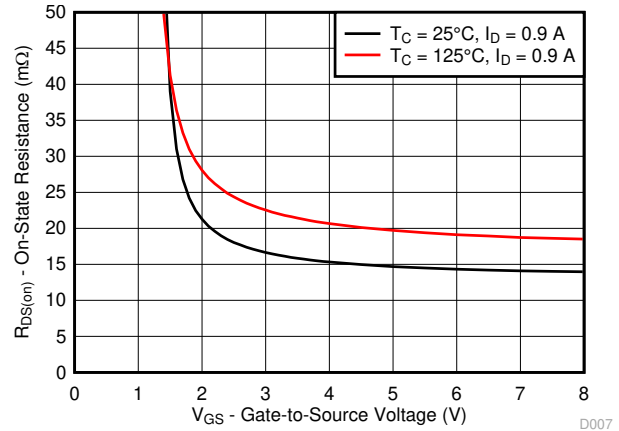


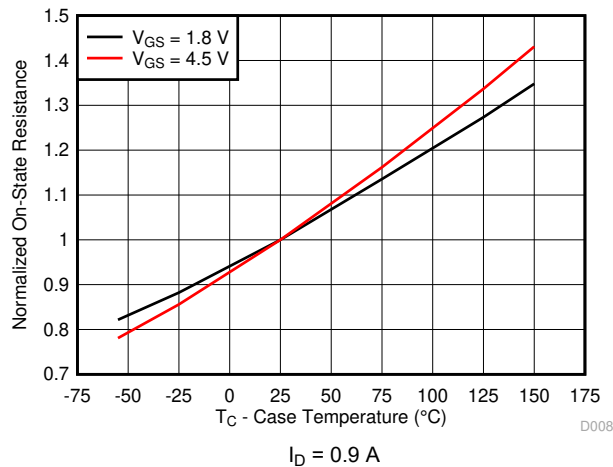
Figure 5-5. Capacitance



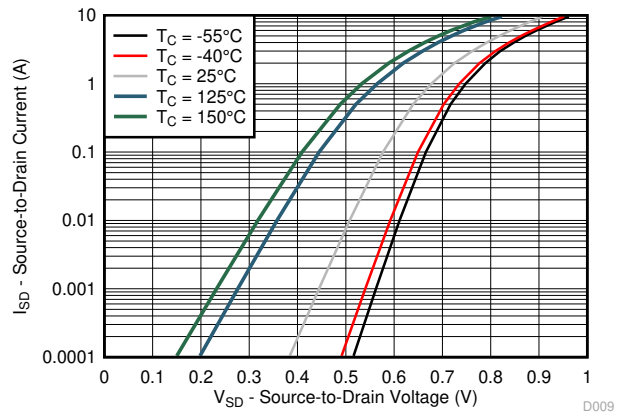
**Figure 5-6. Threshold Voltage vs Temperature**



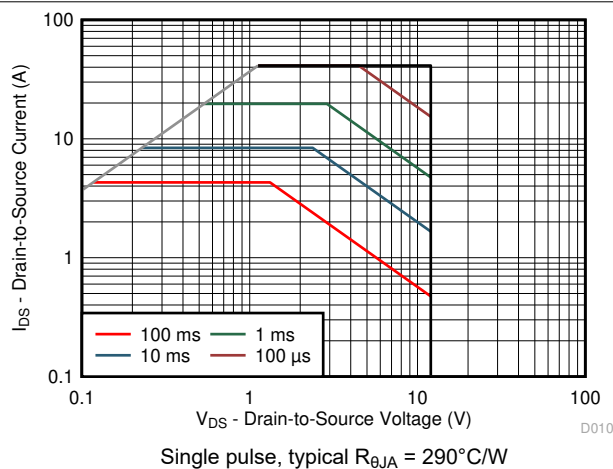
**Figure 5-7. On-State Resistance vs Gate-to-Source Voltage**



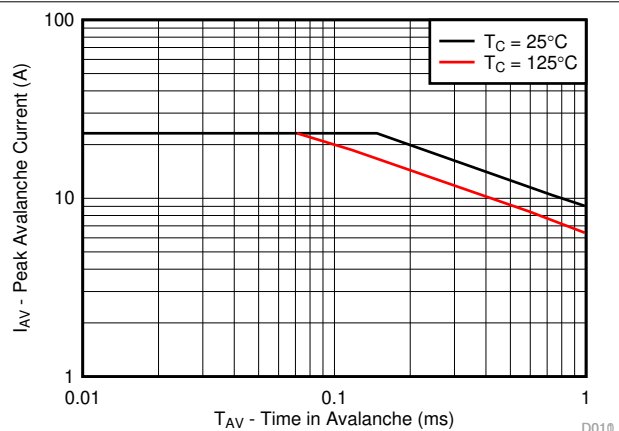
**Figure 5-8. Normalized On-State Resistance vs Temperature**



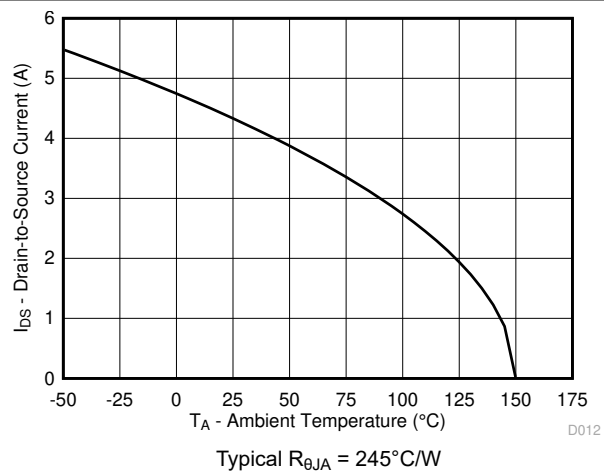
**Figure 5-9. Typical Diode Forward Voltage**



**Figure 5-10. Maximum Safe Operating Area (SOA)**



**Figure 5-11. Single Pulse Unclamped Inductive Switching**

**Figure 5-12. Maximum Drain Current vs Temperature**

## 6 Device and Documentation Support

### 6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 6.2 Trademarks

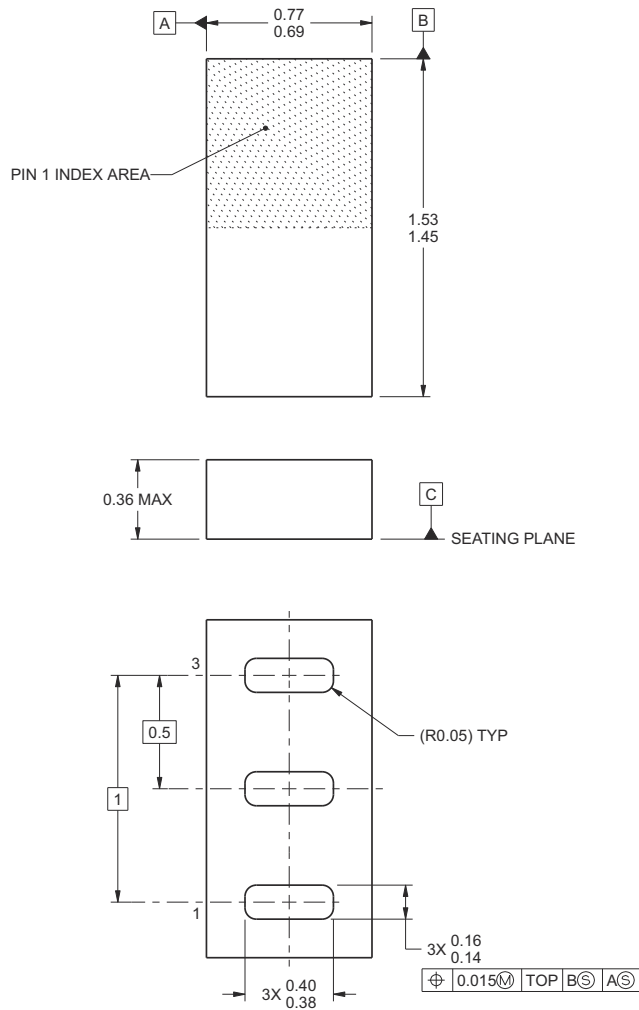
FemtoFET™ is a trademark of Texas Instruments.

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## 7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

### 7.1 Mechanical Dimensions



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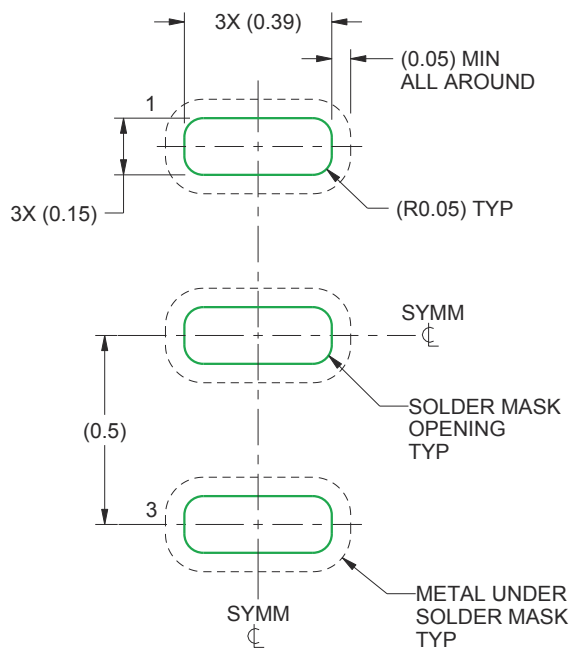
- A. All linear dimensions are in millimeters (dimensions and tolerancing per AME T14.5M-1994).
- B. This drawing is subject to change without notice.
- C. This package is a PB-free solder land design.

**Table 7-1. Pin Configuration**

POSITION	DESIGNATION
Pin 1	Gate
Pin 2	Source
Pin 3	Drain

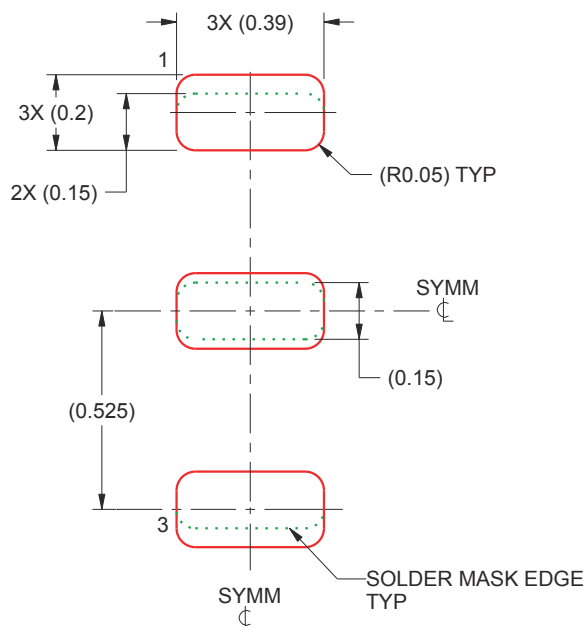


## 7.2 Recommended Minimum PCB Layout



- A. All dimensions are in millimeters.
- B. For more information, see [FemtoFET Surface Mount Guide](#) (SLRA003D).

## 7.3 Recommended Stencil Pattern



- A. All dimensions are in millimeters.

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD13385F5	ACTIVE	PICOSTAR	YJK	3	3000	RoHS & Green	NIAU	Level-1-260C-UNLIM	-55 to 150	4V	<a href="#">Samples</a>
CSD13385F5T	ACTIVE	PICOSTAR	YJK	3	250	RoHS & Green	NIAU	Level-1-260C-UNLIM	-55 to 150	4V	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBsolete:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## TAPE AND REEL INFORMATION



\*All dimensions are nominal

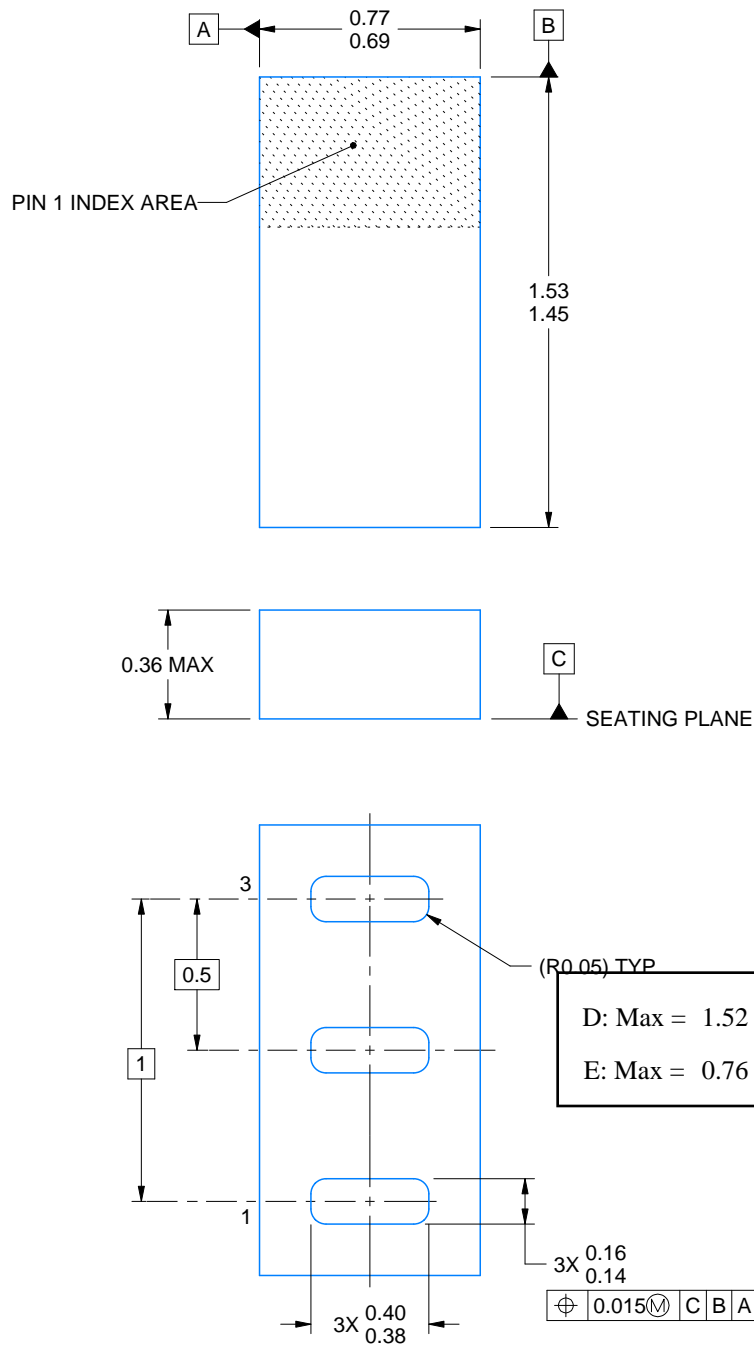
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD13385F5	PICOSTAR	YJK	3	3000	180.0	8.4	0.92	1.68	0.42	4.0	8.0	Q1
CSD13385F5T	PICOSTAR	YJK	3	250	180.0	8.4	0.92	1.68	0.42	4.0	8.0	Q1

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD13385F5	PICOSTAR	YJK	3	3000	182.0	182.0	20.0
CSD13385F5T	PICOSTAR	YJK	3	250	182.0	182.0	20.0

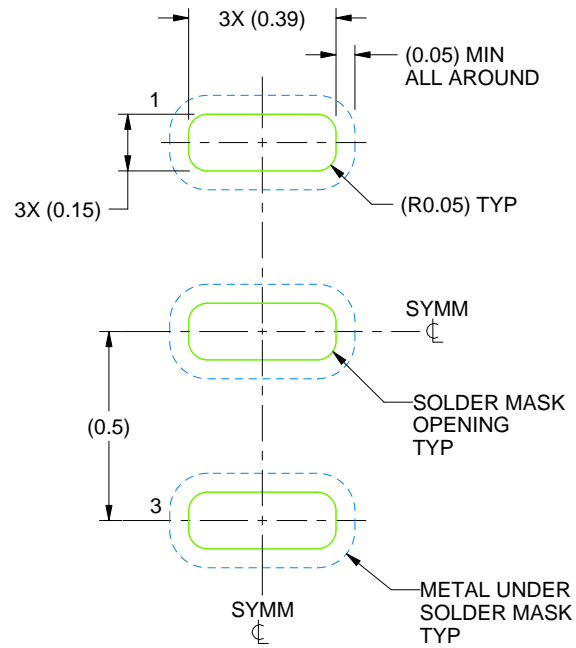


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## NOTES:

PicoStar is a trademark of Texas Instruments.

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M
2. This drawing is subject to change without notice.
3. This package is a Pb-free bump design. Bump finish may vary. To determine the exact finish, refer to the device datasheet or contact a local TI representative.

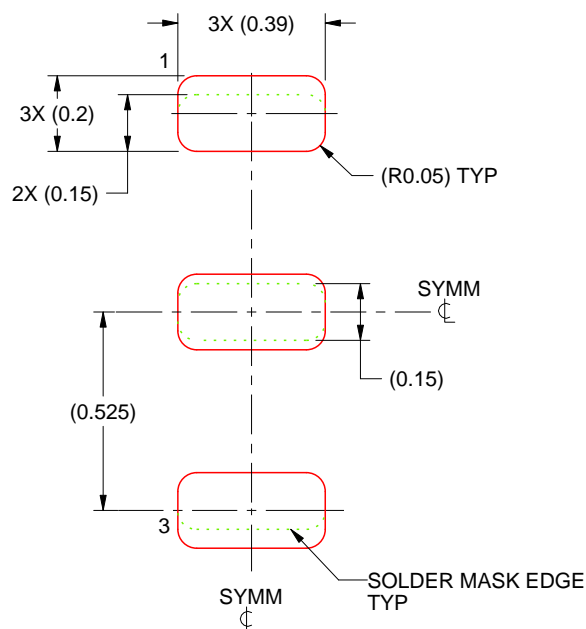


LAND PATTERN EXAMPLE  
SOLDER MASK DEFINED  
SCALE:50X

4222132/C 03/2022

NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/slua271](http://www.ti.com/lit/slua271)).



**SOLDER PASTE EXAMPLE**  
 BASED ON 0.075 - 0.1 mm THICK STENCIL  
 SCALE:50X

NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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